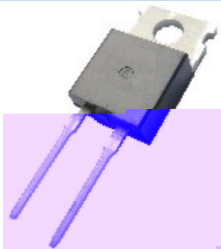
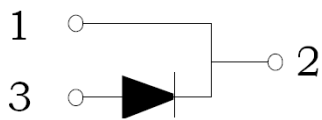


TO-220AC

Ultrafast Recovery Diode in a TO-220AC Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode.



PIN1 2 Cathode

PIN 3 Anode

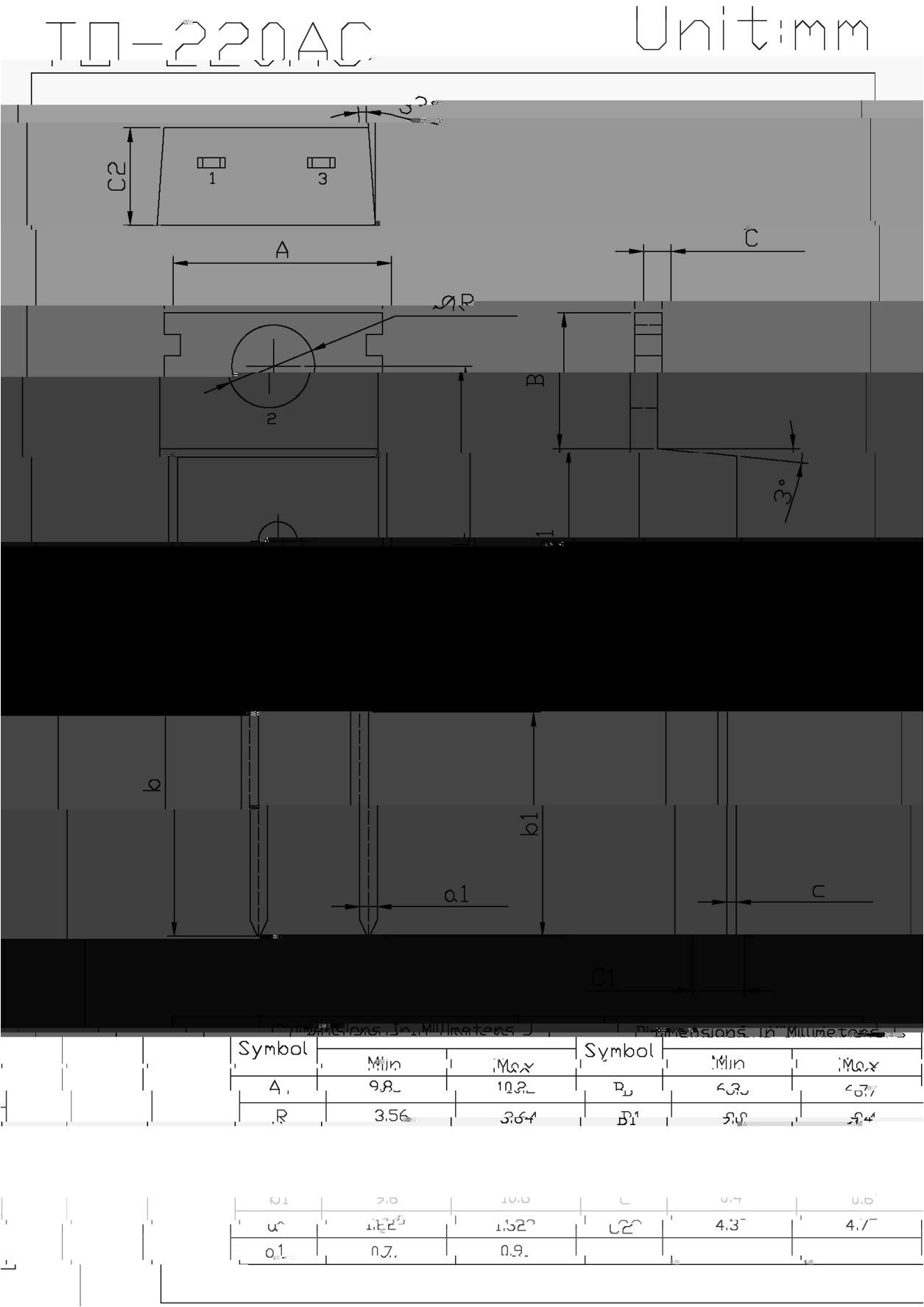
See Marking Instructions

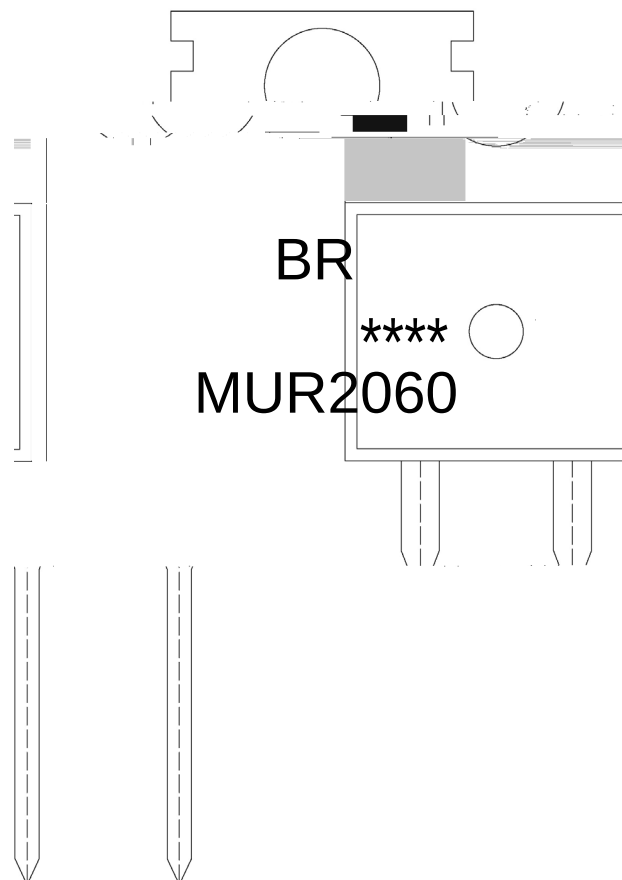
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Average Forward Current	I_F	1 × 20	A
Peak forward surge current	I_{FSM}	250	A
Typical Thermal Resistance Junction to Case	R_{JC}	2.8	/W
Junction Temperature Range	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=5.0A$ $T_C=25$			1.35	V
		$I_F=5.0A$ $T_C=150$			1.15	
		$I_F=20A$ $T_C=25$			1.65	
		$I_F=20A$ $T_C=150$			1.25	
Instantaneous Reverse Current(Note1)	I_R	$V_R=600V$ $T_a=25$			0.25	mA
		$V_R=420V$ $T_a=150$			1.0	
		$V_R=600V$ $T_a=150$			2.0	
Reverse Recovery Time	t_{rr}	$I_F=0.5A$ $I_R=1.0A$ $I_{RR}=0.25A$			50	ns

/Notes

1. / Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip





BR

MUR2060

Note:

BR:

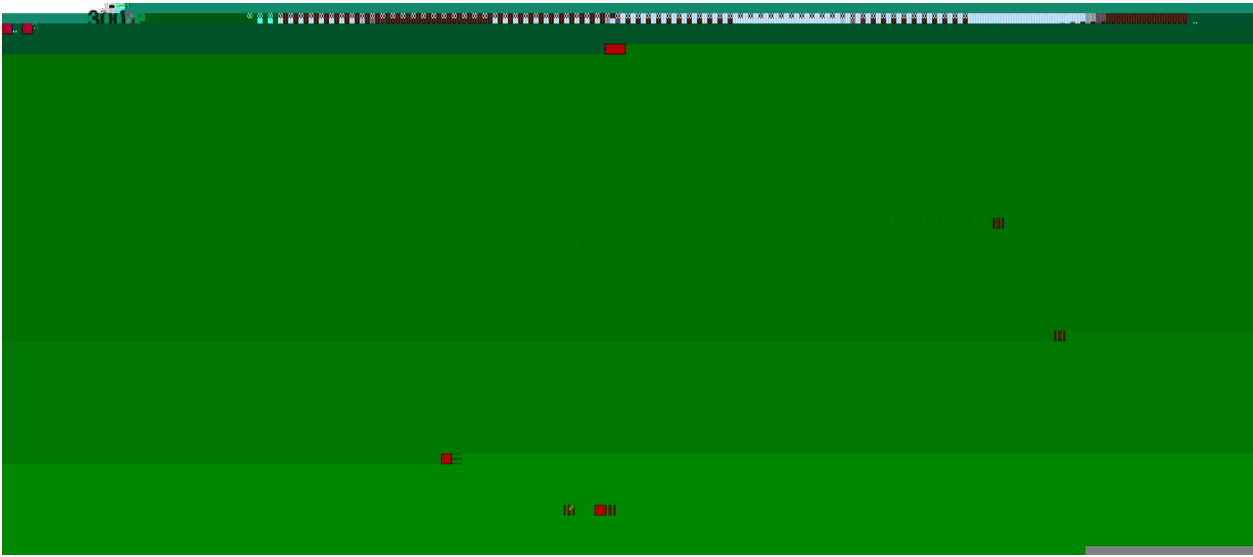
Company Code

MUR2060

Product Type.

****:

Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;

2

255±5

5±0.5sec;

3

2 10

/sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type	Units 包装数量		Dimension 包装尺寸 (unit: mm ³)	
封装形式	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Bags/Inner Box 袋/盒